

**AMENDMENTS TO THE CLAIMS**

1. (Currently Amended) A method of making a semiconductor structure, comprising:  
~~determining~~ calculating a first polish time, sufficient to planarize a layer on a semiconductor substrate;  
polishing the layer for said first polish time, to planarize the layer; and  
polishing the layer to a predetermined thickness.
2. (Currently Amended) The method of claim 1, further comprising, prior to the calculating ~~determining~~ of said first polish time, measuring the thickness of the layer.
3. (Currently Amended) The method of claim 1, further comprising, prior to the calculating ~~determining~~ of said first polish time, measuring ~~the~~ a pattern density of the layer.
4. (Currently Amended) The method of claim 1, further comprising, prior to the calculating ~~determining~~ of said first polish time, identifying ~~the~~ a composition of the layer.
5. (Original) The method of claim 1, further comprising determining a second polish time sufficient to reduce the thickness of the layer after planarization to the predetermined thickness;  
wherein the polishing of the layer to the predetermined thickness comprises polishing the layer for said second polish time.
6. (Currently Amended) A process for making a plurality of semiconductor structures, comprising  
making each semiconductor structure by the method of claim 1;  
wherein ~~the~~ a Cpk of the process is at least 1.
7. (Currently Amended) A process for making a plurality of semiconductor structures, comprising:  
making each semiconductor structure by the method of claim 5;

wherein ~~the~~ a Cpk of the process is at least 1.

8. (Currently Amended) The process of claim 7, wher in the making of each semiconductor structure comprises, prior to the calculating ~~determining~~ of said first polish time, measuring the thickness of the layer, ~~the~~ a pattern density of the layer, and identifying ~~the~~ a composition of the layer.

9-11. (Cancelled)

12. (Currently Amended) In a method of making a semiconductor structure, including polishing a layer by chemical mechanical polishing, the improvement comprising ~~determining~~ calculating a first polish time sufficient to make the layer planar; determining a second polish time to reduce the thickness of the planar layer; and polishing for a third polish time equal to the sum of the first and second polish times.

13. (Original) A method of making a semiconductor device, comprising:  
making a semiconductor structure by the method of claim 1; and  
forming a semiconductor device from said structure.

14. (Original) A method of making an electronic device, comprising:  
making a semiconductor device by the method of claim 13; and  
forming an electronic device, comprising said semiconductor device.

15. (Original) A method of making a semiconductor device, comprising:  
making a semiconductor structure by the method of claim 5; and  
forming a semiconductor device from said structure.

16. (Original) A method of making an electronic device, comprising:  
making a semiconductor device by the method of claim 15; and  
forming an electronic device, comprising said semiconductor device.

17-23. (Cancelled)

24. (Currently Amended) A method of making a semiconductor structure, comprising:

polishing a layer on a semiconductor substrat with ~~the~~ a system,  
comprising:

a chemical mechanical polishing apparatus; and  
machine readable medium, comprising code, imbedded in the  
machine readable medium, for calculating a first polish time, sufficient to  
planarize a layer on a semiconductor substrate. ~~of claim 23.~~

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*incl*
25. (Original) A method of making a semiconductor device, comprising:  
making a semiconductor structure by the method of claim 24; and  
forming a semiconductor device from said structure.
26. (Original) A method of making an electronic device, comprising:  
making a semiconductor device by the method of claim 25; and  
forming an electronic device, comprising said semiconductor device.
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